



6. Phonons

6.1 Specific heat — Debye model:

- assumptions:
- ▶ solids are elastic, isotropic homogenous continua
 - ▶ excitations: **sound waves** with **linear dispersion**
 - ▶ Bose-Einstein distribution

internal energy:

$$U(T) = \int_0^{\hbar\omega_D} \hbar\omega \mathcal{D}(\omega) f(\omega, T) d\omega$$

cut-off frequency → Debye frequency

$\propto \omega^2$

specific heat:

$$C_V = \frac{\partial U}{\partial T} = 9Nk_B \left(\frac{T}{\Theta}\right)^3 \int_0^{x_D} \frac{x^4 e^x}{(e^x - 1)^2} dx$$

$x_D = \hbar\omega_D/k_B T$

$x = \hbar\omega/k_B T$

$\Theta = \hbar\omega_D/k_B$



Limiting cases:

(i) $T \rightarrow \infty \longrightarrow x \rightarrow 0$

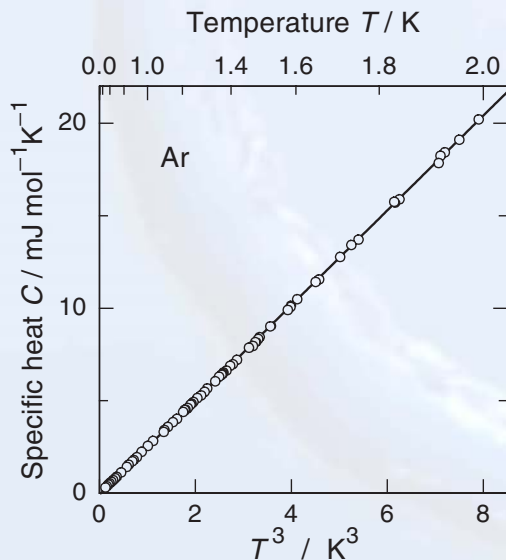
$$\lim_{x \rightarrow 0} \int_0^{x_D} \frac{x^4 e^x}{(e^x - 1)^2} dx \approx \int_0^{x_D} \frac{x^4 \cdot 1}{(1 + x - 1)^2} dx = \frac{x_D^3}{3} = \frac{1}{3} \left(\frac{\Theta}{T} \right)^3$$

$\longrightarrow C_V = 3Nk_B$ Dulong-Petit law

(ii) $T \rightarrow 0 \longrightarrow x_D \rightarrow \infty$

$$C_V = 9Nk_B \left(\frac{T}{\Theta} \right)^3 \underbrace{\int_0^{\infty} \frac{x^4 e^x}{(e^x - 1)^2} dx}_{4\pi^4/15} = \frac{12\pi^4}{5} Nk_B \left(\frac{T}{\Theta} \right)^3$$

$\longrightarrow C_V = \frac{12\pi^4}{5} Nk_B \left(\frac{T}{\Theta} \right)^3$



- ▶ perfect agreement with theory
- ▶ only small temperature range
- ▶ Debye temperature $\Theta = 92 \text{ K}$



6.1 Specific Heat



Element	Θ (K)	Element	Θ (K)	Element	Θ (K)	Element	Θ (K)
Ar	92	Cu	347	Mn	409	Sc	346
Ac*	100	Er	118	Mo	423	Se	152
Ag	227	Fe	477	N*	70	Si	645
Al	433	Ga	325	Na	156	Sm	169
Am	121	Gd	182	Nb	276	Sn	199
As	282	Ge	373	Nd	163	Sr	147
Au	162	H (para)	122	Ne	75	Ta	245
B	1480	H (orth)	114	Ni	477	Tb	176
Ba	111	³ He	19–33	Np	259	Te	152
Be	1481	Hf	252	O*	90	Th	160
Bi	120	Hg	72	Os	467	Ti	420
C (Dia.)	2250	Ho	190	Pa	185	Tl	78
C (Gra.)	413	I	109	Pb	105	Tm	200
Ca	229	In	112	Pd	271	U	248
Cd	210	Ir	420	Pr	152	V	399
Ce	179	K	91	Pt	237	W	383
Cl*	115	Kr	72	Rb	56	Xe	64
Cm	123	La	145	Re	416	Y	248
Co	460	Li	344	Rh	512	Yb	118
Cr	606	Lu	183	Ru	555	Zn	329
Cs	40	Mg	403	Sb	220	Zr	290



Compound	θ (K)	Compound	θ (K)	Compound	θ (K)
AgBr*	140	Cr ₂ Cl ₃ *	360	MgO*	800
AgCl*	180	FeS ₂ *	630	MoS ₂ *	290
As ₂ O ₃ *	140	KBr	173	RbBr	131
As ₂ O ₅ *	240	KCl	235	RbCl	165
AuCu ₃	285	KI	131	RbI	103
BN*	600	InSb	206	SiO ₂ (Quartz)	470
CaF ₂	508	LiF	736	TiO ₂ * (Rutile)	450
CrCl ₂ *	80	LiCl	422	ZnS	315

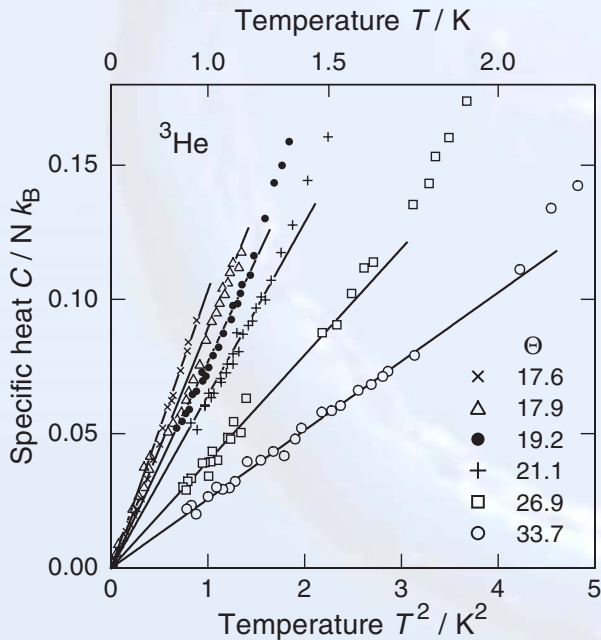
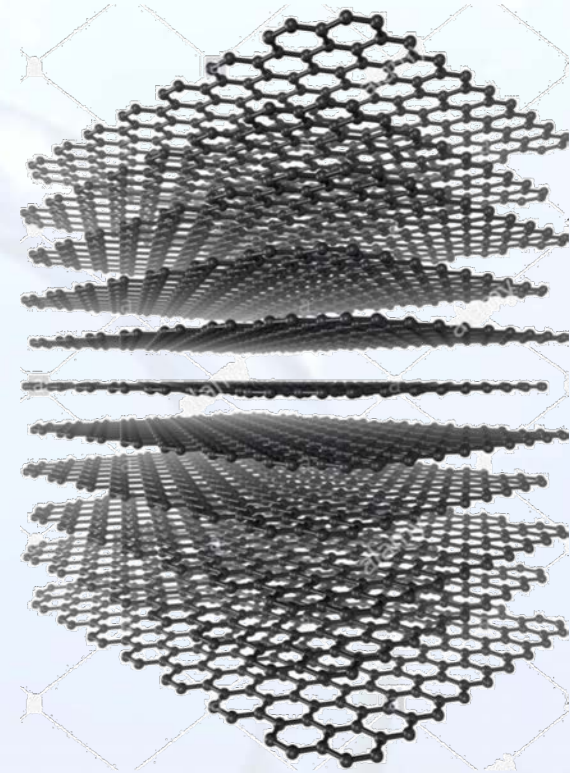


low-dimensional systems

$$D(\omega) \propto \omega^{d-1} \longrightarrow C_V \propto T^d$$

$$d = 2 \longrightarrow C_V \propto T^2.$$

example: ^3He atoms on **graphite** (sub-mono layers)



- ▶ high temperatures and **low densities** \longrightarrow gas: $C_V \approx Nk_B$
- ▶ for $n > 0.078 \text{ \AA}^{-2}$ \longrightarrow two-dimensional **solid** crystals
- ▶ increasing density \longrightarrow Θ increases
- ▶ density $0.078 \dots 0.092 \text{ \AA}^{-2}$ \longrightarrow $\Theta = 17.6 \dots 37.7 \text{ K}$
- ▶ at high temperatures **melting** of 2d-crystals



6.2 Heat transport

Fourier equation $\mathbf{j} = -\Lambda \nabla T$

$$\Lambda = \frac{1}{3} C v \ell$$

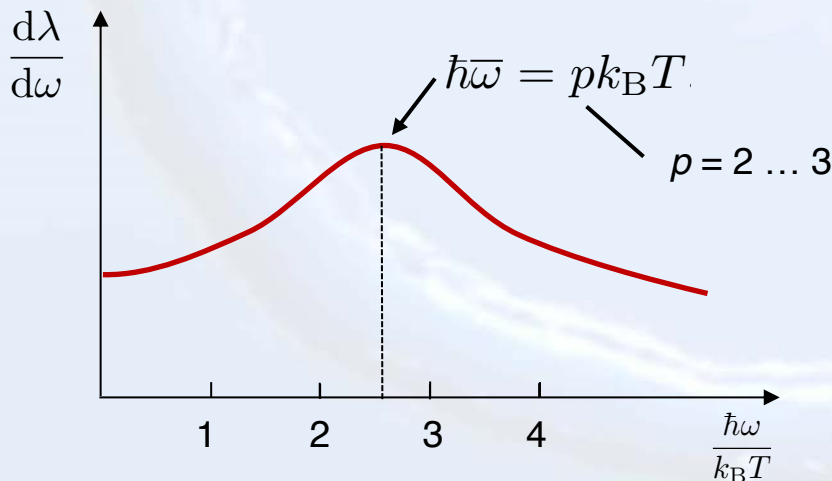
in general

$$\Lambda = \frac{1}{3} \sum_i \int c_i(\omega) v_i(\omega) \ell_i(\omega) d\omega$$

different "particles"
phonon branches

spectral specific heat

dominate phonon approximation (Debye)



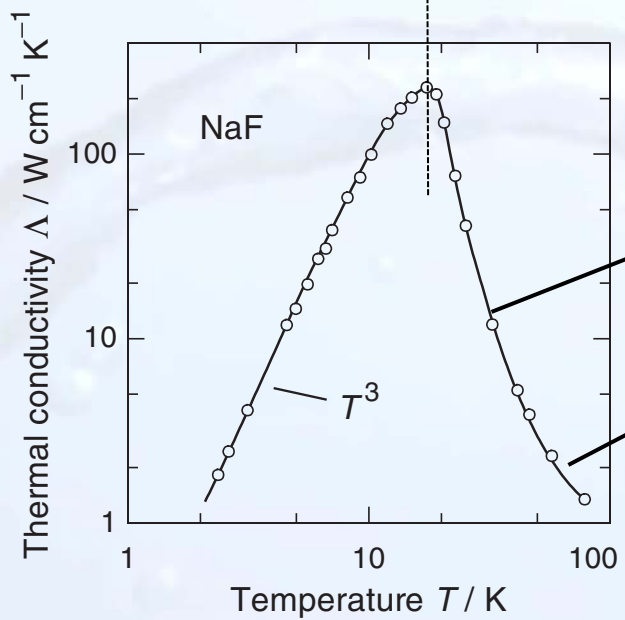
- ▶ summation and integration can be avoided
- ▶ in addition: linear dispersion



6.2 Heat Transport



phonon-defect scattering ← → phonon-phonon scattering

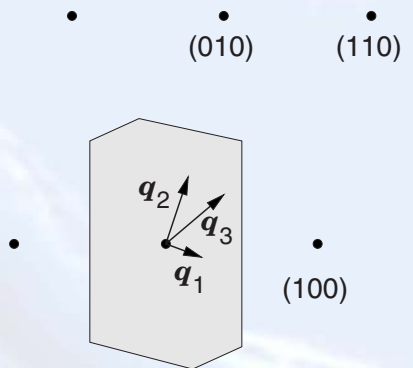


$\Delta \propto l_U \propto e^{\Theta/2T}$

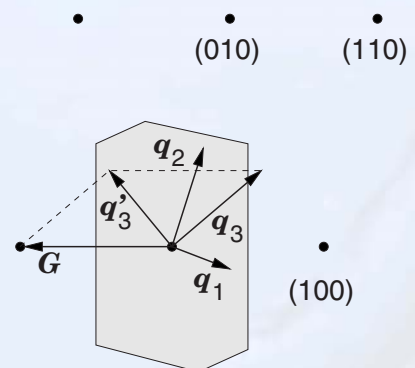
$\Delta \propto T^{-1}$

number of umklapp processes **increases** with temperature

normal process



umklapp process

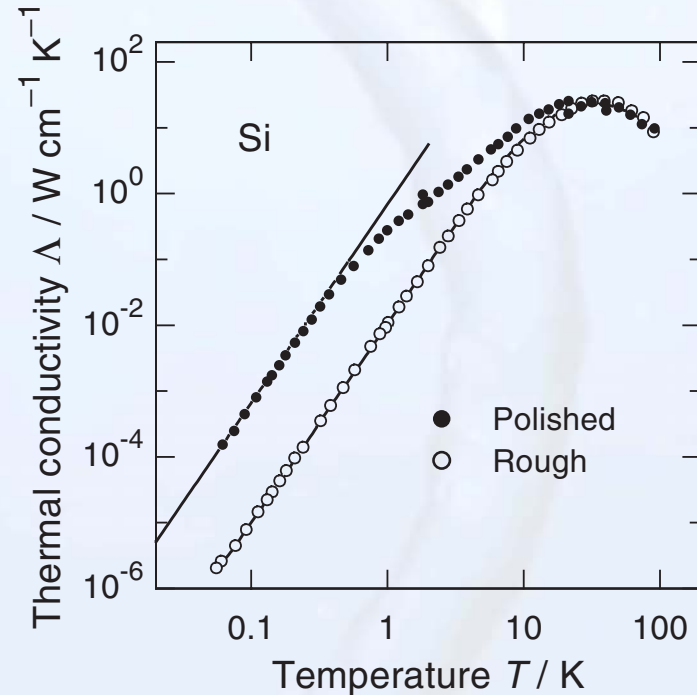
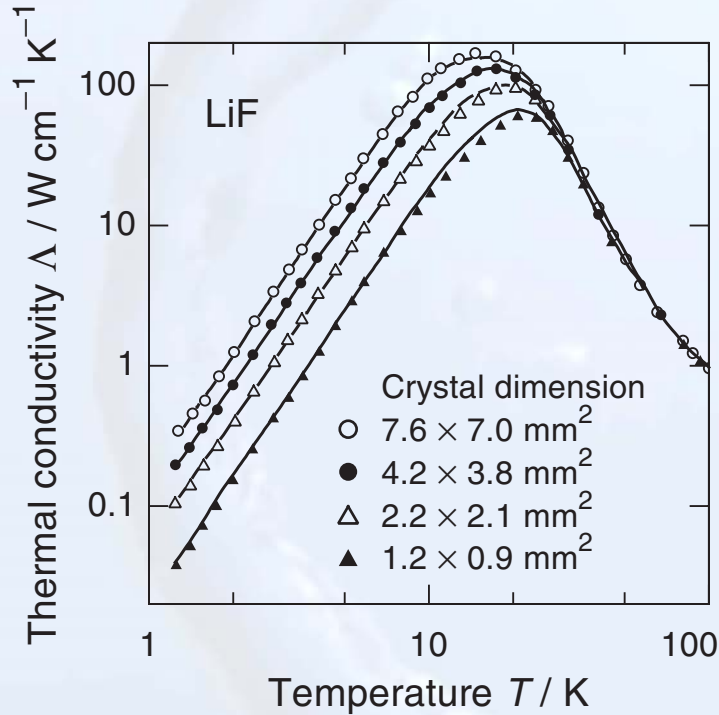




phonon-defect scattering

a) surfaces

$$\Lambda = \frac{1}{3} C v l \quad \xrightarrow{l \approx d} \quad \Lambda \approx \frac{1}{3} C_V v d \propto T^3 \quad \text{Casimir regime}$$



- ▶ depends on sample cross-section
- ▶ temperature dependence as expected

- ▶ roughed: mean free path factor 50 shorter
- ▶ polished: mean free path 7 cm, sample length

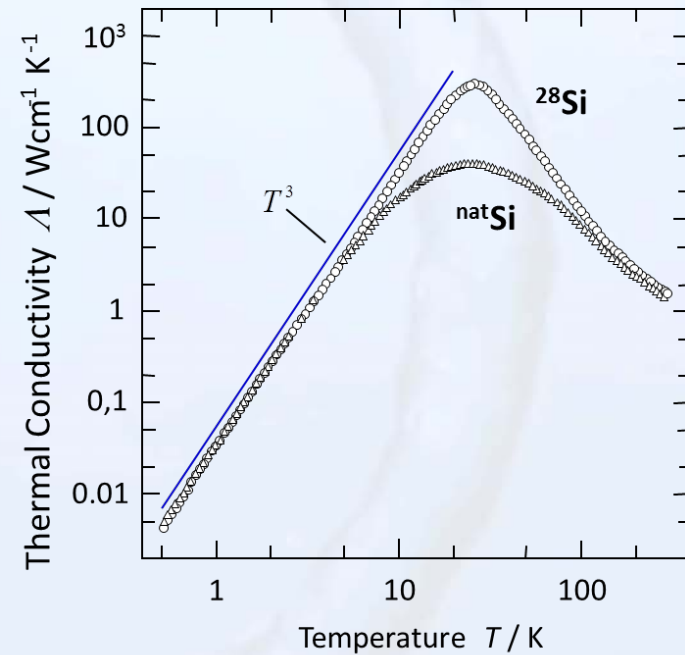
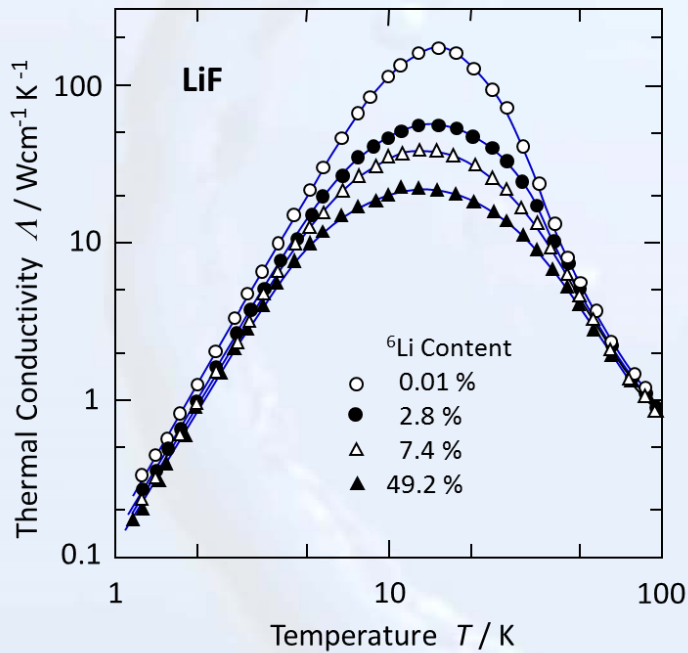


b) influence of point defects (elastic scattering)

→ Rayleigh scattering, since $\lambda_{\text{phonon}} \gg d_{\text{defect}}$

$$\ell^{-1} = \frac{n_p V_A^2}{4\pi} \left(\frac{\Delta M}{M} \right)^2 q^4 \propto \omega^4$$

is important at intermediate temperatures, since at low temperature q is too small and at high temperatures phonon-phonon scattering dominates



- ▶ adding ⁶Li **reduces** heat transport
- ▶ **maximum** becomes **rounded**

- ▶ ^{nat}Si: 10% of all Si atoms have mass difference
- ▶ ²⁸Si: sharp peak → little scattering on point defects